

2SB679

SILICON PNP TRIPLE DIFFUSED TYPE
(DARLINGTON POWER)

INDUSTRIAL APPLICATIONS

LOW FREQUENCY MEDIUM POWER AMPLIFIER AND
MEDIUM SPEED SWITCHING APPLICATIONS.

PULSE MOTOR DRIVE, RELAY DRIVE AND HAMMER
DRIVE APPLICATIONS.

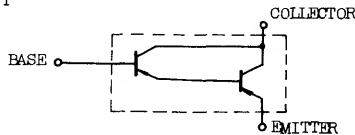
FEATURES :

- High DC Current Gain : $h_{FE(2)}=1000(\text{Min.})$
($V_{CE}=-2V$, $I_C=-1A$)
- Low Saturation Voltage : $V_{CE(sat)}=-1.5V(\text{Max.})$ ($I_C=-1A$)
- Complementary to 2SD689.

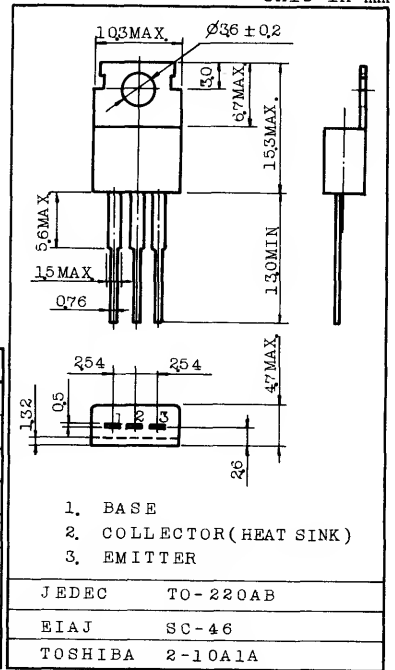
MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-100	V
Collector-Emitter Voltage	V_{CEO}	-100	V
Emitter-Base Voltage	V_{EBO}	-10	V
Collector Current	I_C	-1.5	A
Emitter Current	I_E	1.5	A
Collector Power Dissipation ($T_c = 25^\circ\text{C}$)	P_C	10	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$

EQUIVALENT CIRCUIT



Unit in mm



Mounting kit No.AC75

Weight : 1.9g

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=-100V$, $I_E=0$	-	-	-10	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=-10V$, $I_C=0$	-	-	-10	μA
Breakdown Voltage	Collector-Emitter	$V_{(BR)CEO}$ $I_C=-10mA$, $I_B=0$	-100	-	-	V
	Emitter-Base	$V_{(BR)EBO}$ $I_E=-5mA$, $I_C=0$	-10	-	-	
DC Current Gain		$h_{FE(1)}$ $V_{CE}=-2V$, $I_C=-0.1A$	2000	-	-	
		$h_{FE(2)}$ $V_{CE}=-2V$, $I_C=-1A$	1000	-	-	
Saturation Voltage	Collector-Emitter	$V_{CE(sat)}$ $I_C=-1A$, $I_B=-2mA$	-	-	-1.5	V
	Base-Emitter	$V_{BE(sat)}$ $I_C=-1A$, $I_B=-2mA$	-	-	-2.5	
Switching Time	Turn-on Time	t_{on}	-	0.3	-	μs
	Storage Time	t_{stg}	-	2.0	-	
	Fall Time	t_f	-	0.7	-	

TOSHIBA CORPORATION